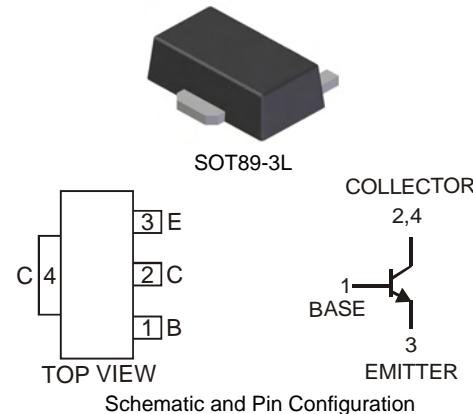


Features

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)**

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	25	—	—	V	$I_C = 1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	—	V	$I_C = 10\mu\text{A}, I_C = 0$
Collector-Base Cutoff Current	I_{CBO}	—	—	100	nA	$V_{CB} = 20\text{V}, I_E = 0$
Emitter-Base Cutoff Current	I_{EBO}	—	—	100	nA	$V_{EB} = 4.0\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h_{FE}	200 65	—	400	—	$V_{CE} = 2.0\text{V}, I_C = 0.1\text{A}$ $V_{CE} = 2.0\text{V}, I_C = 1.5\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(\text{SAT})}$	—	0.12	0.4	V	$I_C = 1.5\text{A}, I_B = 75\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(\text{SAT})}$	—	0.9	1.2	V	$I_C = 1.5\text{A}, I_B = 75\text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	—	300	—	MHz	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$, $f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	16	—	pF	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$
SWITCHING CHARACTERISTICS						
Turn On Time	t_{on}	—	70	—	ns	$V_{CE} = 12\text{V}, V_{BE} = 5\text{V}$, $I_{B1} = I_{B2} = 25\text{mA}, I_C = 500\text{mA}$
Storage Time	t_{stg}	—	170	—	ns	
Fall Time	t_f	—	25	—	ns	

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
- Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

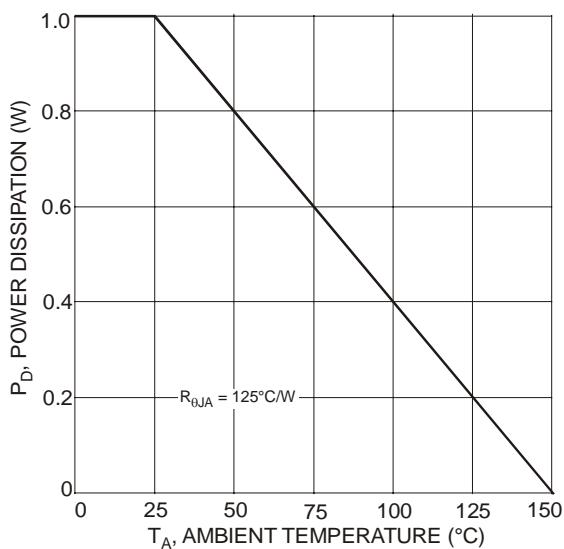


Fig. 1 Power Dissipation vs.
Ambient Temperature (Note 3)

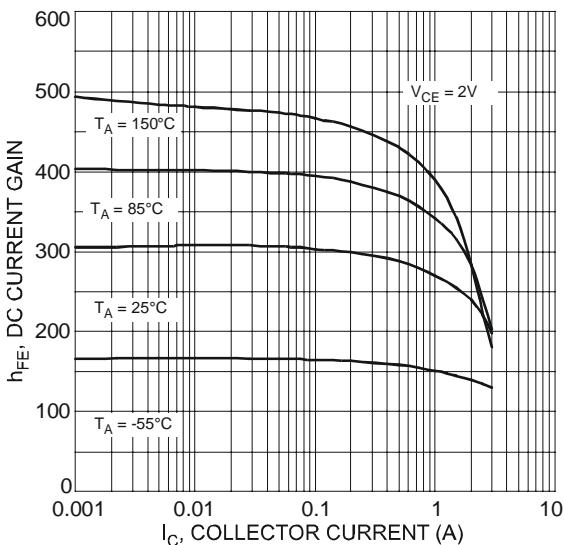


Fig. 3 Typical DC Current Gain vs. Collector Current

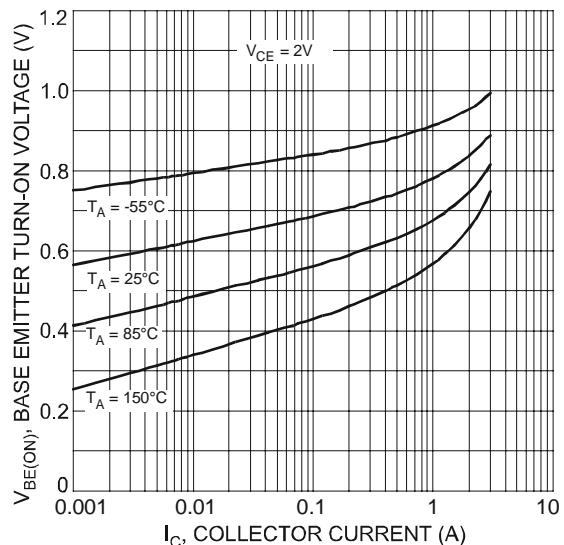


Fig. 5 Typical Base-Emitter Turn-On Voltage
vs. Collector Current

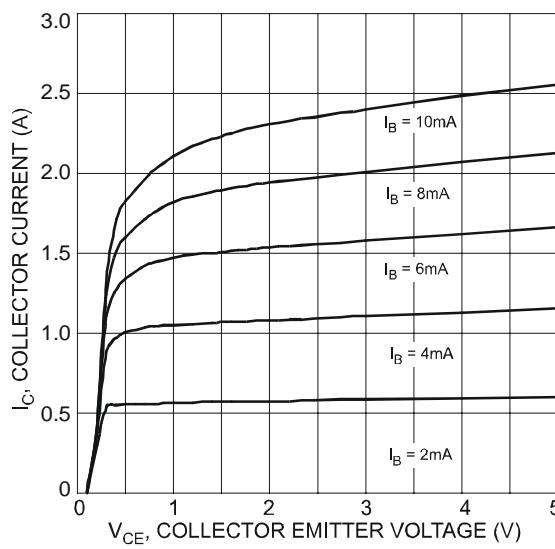


Fig. 2 Typical Collector Current
vs. Collector-Emitter Voltage

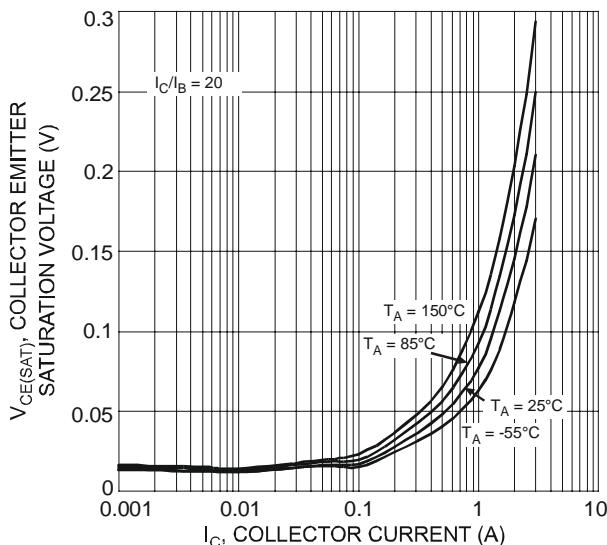


Fig. 4 Typical Collector-Emitter Saturation Voltage
vs. Collector Current

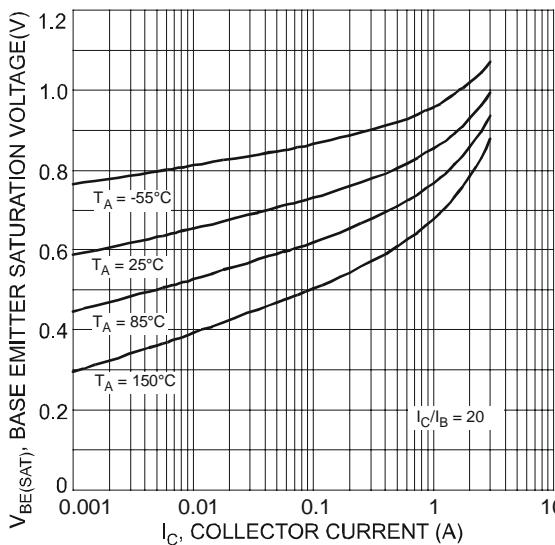


Fig. 6 Typical Base-Emitter Saturation Voltage
vs. Collector Current

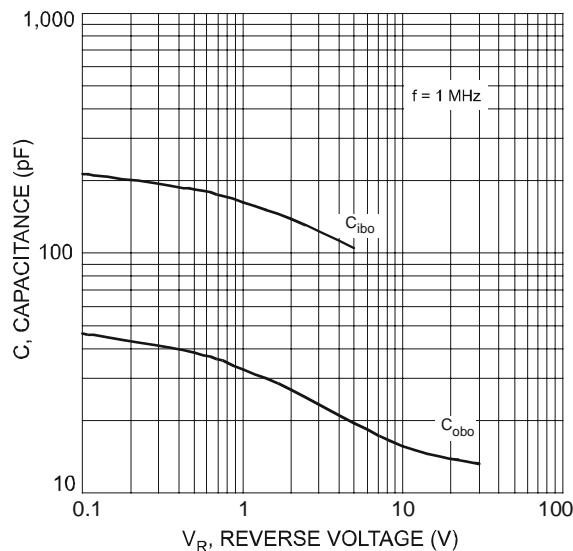


Fig. 7 Typical Junction Capacitance Characteristics

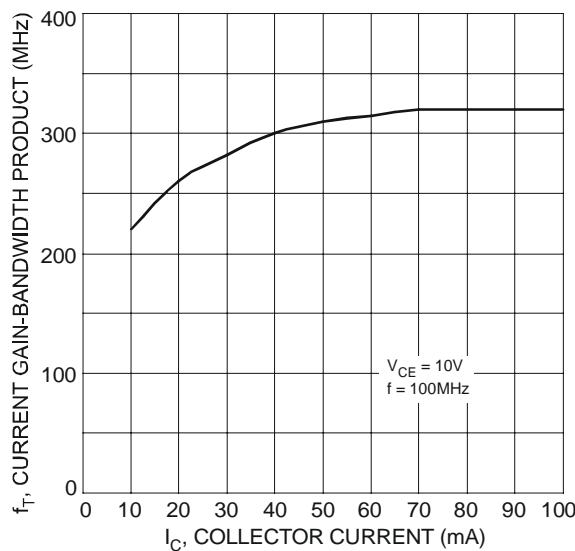


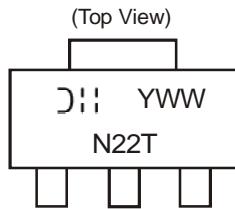
Fig. 8 Typical Gain-Bandwidth Product
vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
2DD1621T-13	SOT89-3L	2500/Tape & Reel

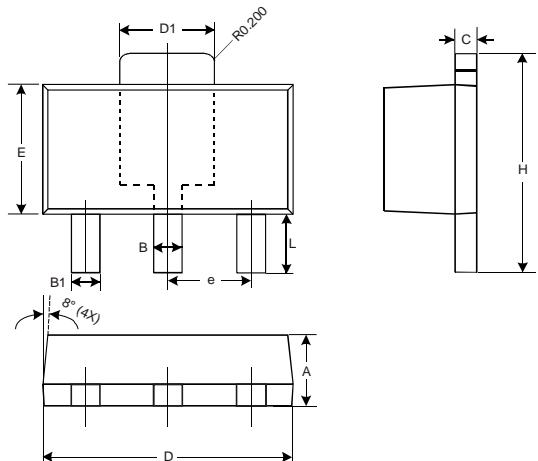
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/ap02007.pdf>.

Marking Information



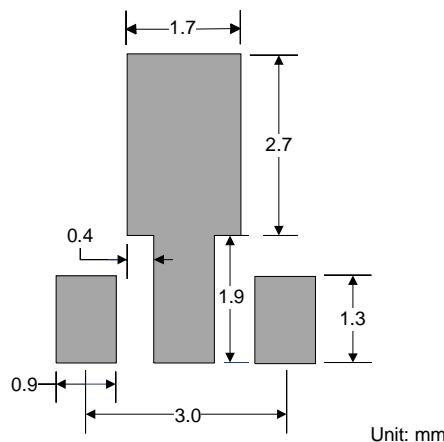
N22T = Product Type Marking Code
YWW = Date Code Marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05

All Dimensions in mm

Suggested Pad Layout**IMPORTANT NOTICE**

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